查询"2SK3582TK"供应函 Field Effect Transistor Silicon N Channel Junction Type

# 2SK3582TK

#### For ECM

Application for Ultra-compact ECM

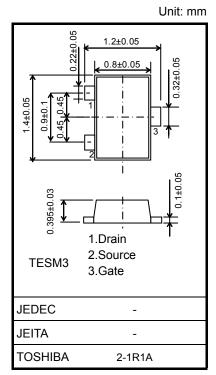
### **Absolute Maximum Ratings (Ta=25°C)**

Characteristic	Symbol	Rating	Unit	
Gate-Drain voltage	$V_{GDO}$	-20	V	
Gate Current	IG	10	mA	
Drain power dissipation (Ta = 25°C)	PD	100	mW	
Junction Temperature	Tj	125	°C	
Storage temperature range	T <sub>stg</sub>	-55~125	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling

Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

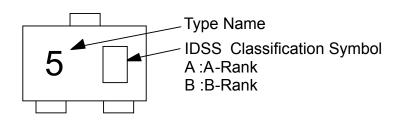


Weight: 2.2mg (typ.)

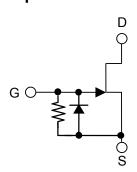
#### **IDSS CLASSIFICATION**

A-Rank 80 to 200 μA B-Rank 170 to 300μA

### Marking



### **Equivalent Circuit**





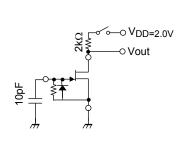
# Elegtrical 6 paracteristics (Ta=25°C)

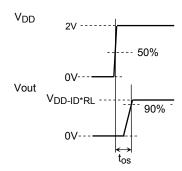
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain Current	I <sub>DSS</sub>	$V_{DS} = 2 V$ , $V_{GS} = 0$	80	_	300	μΑ
Drain Current	I <sub>D</sub>	$V_{DD} = 2 \text{ V, RL= } 2k\Omega, \text{Cg} = 10 \text{pF}$	_	_	340	μA
Gate-Source Cut-off Voltage	V <sub>GS(OFF)</sub>	$V_{DS} = 2 \text{ V}, I_D = 1 \mu A$	-0.1	_	-0.65	V
Forward transfer admittance	Y <sub>fs</sub>	$V_{DS} = 2 \text{ V}, V_{GS} = 0 \text{ V}$	0.55	1.0	_	mS
Gate-Drain Voltage	V <sub>(BR)GDO</sub>	IG=-10μA	-20	_	_	V
Input capacitance	C <sub>iss</sub>	$V_{DS} = 2 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	3.6	_	pF
Voltage Gain	Gv	$V_{DD} = 2V$ , RL= $2k\Omega$ ,Cg = $10pF$ , f = $1kHz$ ,vin= $100mV$	-5.0	0	+2.0	dB
Delta Voltage Gain	DGv(f)	$V_{DD} = 2V$ , RL= $2k\Omega$ ,Cg = $10pF$ ,f = $1kHz$ to $100Hz$ ,vin= $100mV$	_	0	-1.0	dB
Delta Voltage Gain	DGv(V)	$V_{DD} = 2V$ to 1.5V, RL= $2k\Omega$ , Cg = $10pF$ , $f = 1kHz$ , $vin=100mV$	_	-1.0	-3.0	dB
Noise Voltage	VN	V <sub>DD</sub> = 2V, RL= 1kΩ,Cg = 10pF,Gv=80dB, A-Curve Filter	_	_	50	mV
Total Harmonic Distortion	THD	$V_{DD} = 2V$ , RL= $2k\Omega$ ,Cg = $10pF$ , f = $1kHz$ , vin= $50mV$	_	1.0	_	%
Time Output Stability	tos	$V_{DD} = 2V$ , RL= $2k\Omega$ ,Cg = $10pF$	_	100	200	ms

# **Time Output Stability Test Method**

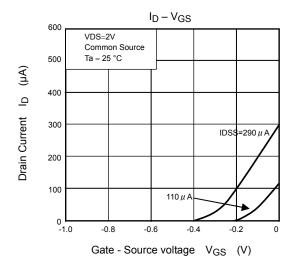
### a) TEST CIRCUIT

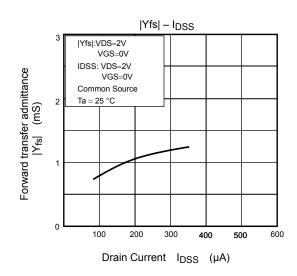
### b) TEST SIGNAL

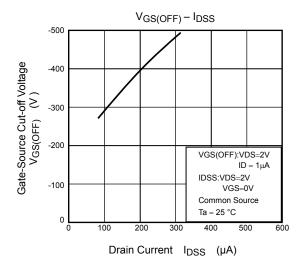


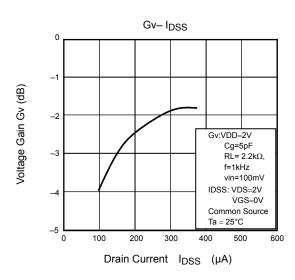


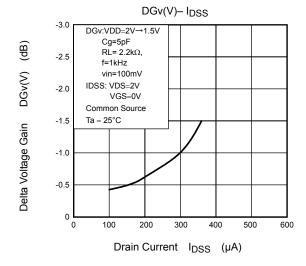
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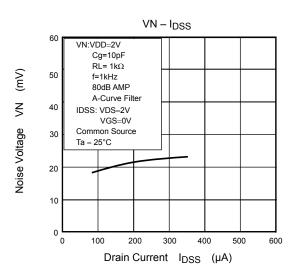






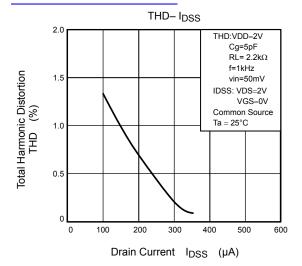


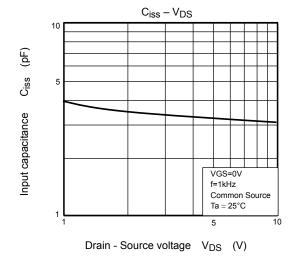




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